ERRATUM

Erratum to: Series and parallel resistance effects on the C–V and G–V characteristics of Al/SiO₂/Si structure

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Unfortunately, the original publication of the article contained a mistake in the model part of Equation 1 under “Theory of the MOS structure” section.

I am grateful to Professor Matoussi Adel for pointing out the error in this equation.

The corrected Eq. 1 is given as follows:

$$Y = G_{\text{MOS}} + j\omega C_{\text{MOS}} = \frac{1}{R_s + \frac{1}{j\omega C_{ox}} + \frac{1}{\left(j\omega C_{sc} + \frac{1}{R_p}\right)}} \quad (1)$$

The online version of the original article can be found under doi:[10.1007/s10825-016-0844-z](https://doi.org/10.1007/s10825-016-0844-z).

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